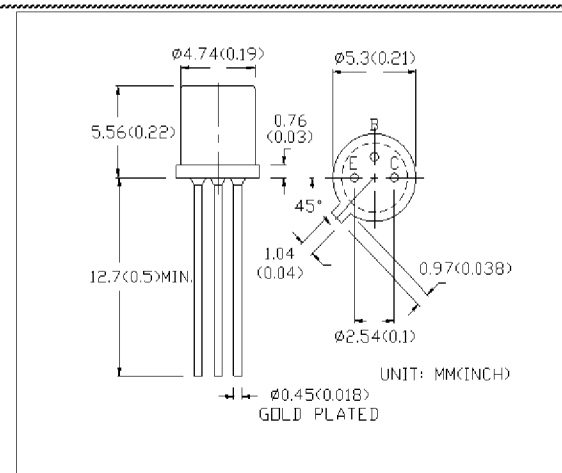


DESCRIPTION

2N4029 is PNP silicon planar epitaxial transistor for AF medium power drivers and outputs.



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	80V
Collector-Emitter Voltage	VCEO	80V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	1A
Continuous Power Dissipation	Pd	800mW
Operating & Storage Junction Temperature	Tj,Tstg	-65 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	80		V	IC = 10μA IE = 0
Collector-Emitter Breakdown Voltage	LVCEO*	80		V	IC = 10mA IB = 0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE = 10μA IC = 0
Collector Cutoff Current	ICBO		50	nA	VCB = 60V IE = 0
D.C. Current Gain	HFE*	75			IC = 0.1mA VCE = 5V
		100	300		IC = 100mA VCE = 5V
		70			IC = 500mA VCE = 5V
		25			IC = 1A VCE = 5V
Collector-Emitter Saturation Voltage	VCE(sat)*		0.15	V	IC = 150mA IB = 15mA
			0.5	V	IC = 500mA IB = 50mA
Base-Emitter Saturation Voltage	VBE(sat)*		0.9	V	IC = 150mA IB = 15mA
Base-Emitter Voltage	VBE*		1.1	V	IC = 500mA VCE = 0.5V
Current Gain Bandwidth Product	fT	150		MHz	IC = 50mA VCE = 10V
Output Capacitance	Cob		20	pF	VCB = 10V f = 1MHz
Input Capacitance	Cib		110	pF	VEB = 0.5V f = 1MHz

* Pulse test : pulse width < 300μS, duty cycle < 2%.



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